

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

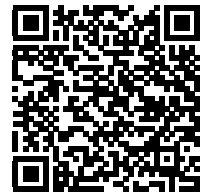
Part Number: VS-GT80DA60U
Manufacturer: Vishay General Semiconductor - Diodes Division
Package: SOT-227-4, miniBLOC
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/vishay-general-semiconductor-diodes-division-vs-gt80da60u.html>

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Contact Information

Email: info@antrexco.com

WhatsApp: +86-186-8066-5326

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Insulated Gate Bipolar Transistor (Trench IGBT), 600 V, 80 A


SOT-227

FEATURES

- High speed trench gate field-stop IGBT positive temperature coefficient
- T_J maximum = 175 °C
- FRED Pt® anti-parallel diodes with ultrasoft reverse recovery
- Fully isolated package
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRIMARY CHARACTERISTICS

V_{CES}	600 V
I_C DC	80 A at $T_C = 97$ °C
$V_{CE(on)}$ typical at 80 A, 25 °C	1.83 V
I_F (DC)	56 A at $T_C = 100$ °C
Speed	8 kHz to 30 kHz
Package	SOT-227
Circuit configuration	Single switch with AP diode

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and safe paralleling
- Direct mounting to heatsink
- Plug-in compatible with other SOT-227 packages
- Lower conduction losses and switching losses
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25$ °C	123	A
		$T_C = 90$ °C	85	
Pulsed collector current	I_{CM}		315	
Diode continuous forward current	I_F	$T_C = 25$ °C	85	
		$T_C = 90$ °C	60	
Gate-to-emitter voltage	V_{GE}		± 20	V
Power dissipation, IGBT	P_D	$T_C = 25$ °C	454	W
		$T_C = 90$ °C	258	
Power dissipation, diode	P_D	$T_C = 25$ °C	238	
		$T_C = 90$ °C	135	
Isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V

**ELECTRICAL SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CEs)}$	$V_{GE} = 0\text{ V}$, $I_C = 2.0\text{ mA}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 80\text{ A}$	-	1.83	2.45	
		$V_{GE} = 15\text{ V}$, $I_C = 80\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.12	-	
		$V_{GE} = 15\text{ V}$, $I_C = 80\text{ A}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	2.2	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 1.0\text{ mA}$	4.6	5.6	7.5	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 1.0\text{ mA}$ ($25\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$)	-	-18.8	-	mV/ $^{\circ}\text{C}$
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$	-	0.2	100	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	51	-	
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	259	-	
Forward voltage drop, diode	V_{FM}	$I_F = 80\text{ A}$, $V_{GE} = 0\text{ V}$	-	1.92	3.15	V
		$I_F = 80\text{ A}$, $V_{GE} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.61	-	
		$I_F = 80\text{ A}$, $V_{GE} = 0\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	1.54	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 250	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Input capacitance	C _{iss}	V _{GE} = 0 V, V _{CE} = 25 V, f = 1.0 MHz		-	10 800	-	pF
Output capacitance	C _{oss}			-	390	-	
Reverse transfer capacitance	C _{rss}			-	220	-	
Total gate charge (turn-on)	Q _g	I _C = 80 A, V _{CC} = 480 V, V _{GE} = 15 V		-	448	-	nC
Gate to emitter charge (turn-on)	Q _{ge}			-	76	-	
Gate to collector charge (turn-on)	Q _{gc}			-	184	-	
Turn-on switching loss	E _{on}	I _C = 80 A, V _{CC} = 300 V, V _{GE} = 15 V, R _g = 27 Ω, L = 500 μH, T _J = 25 °C	Energy losses include tail and diode recovery.	-	1.95	-	mJ
Turn-off switching loss	E _{off}			-	1.25	-	
Total switching loss	E _{tot}			-	3.2	-	
Turn-on delay time	t _{d(on)}			-	120	-	ns
Rise time	t _r			-	90	-	
Turn-off delay time	t _{d(off)}			-	442	-	
Fall time	t _f			-	35	-	mJ
Turn-on switching loss	E _{on}			-	2.3	-	
Turn-off switching loss	E _{off}			-	1.43	-	
Total switching loss	E _{tot}			-	3.73	-	
Turn-on delay time	t _{d(on)}	I _C = 80 A, V _{CC} = 300 V, V _{GE} = 15 V, R _g = 27 Ω, L = 500 μH, T _J = 125 °C		-	124	-	ns
Rise time	t _r			-	94	-	
Turn-off delay time	t _{d(off)}			-	455	-	
Fall time	t _f			-	43	-	
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _R = 200 V		-	69	-	ns
Diode peak reverse current	I _{rr}			-	4.9	-	A
Diode recovery charge	Q _{rr}			-	169	-	nC
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _R = 200 V, T _J = 125 °C		-	139	-	ns
Diode peak reverse current	I _{rr}			-	12.2	-	A
Diode recovery charge	Q _{rr}			-	856	-	nC

**THERMAL AND MECHANICAL SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction temperature range	T_J		-40	-	175	°C
Storage temperature range	T_{Stg}		-40	-	150	°C
Junction-to-case	R_{thJC}	IGBT	-	-	0.33	°C/W
			-	-	0.63	
Case-to-heatsink	R_{thCS}	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf. in)
Case style	SOT-227					

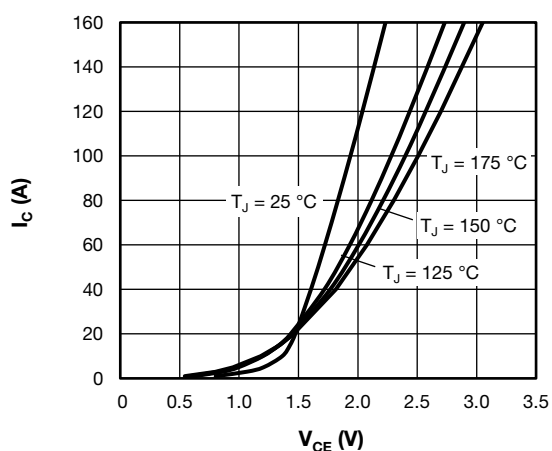
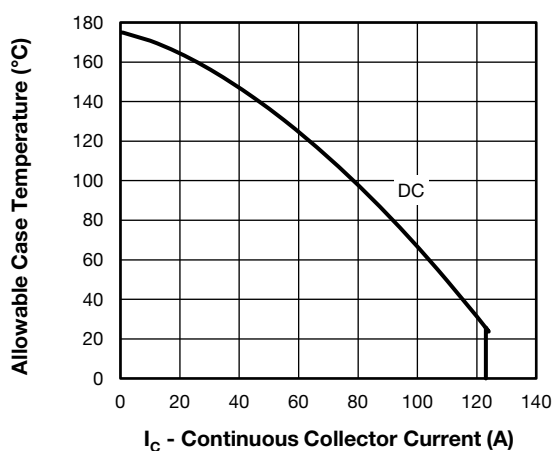
Fig. 1 - Typical IGBT Output Characteristics, $V_{GE} = 15\text{ V}$ 

Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

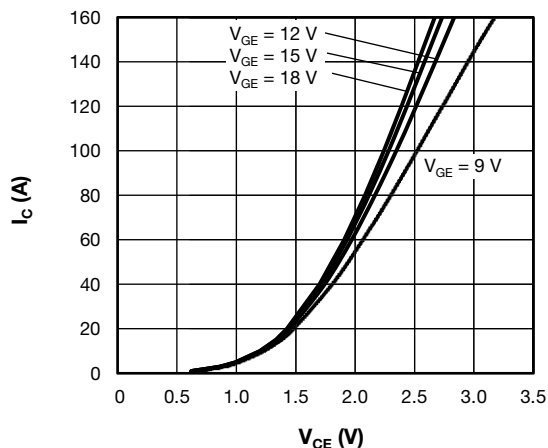
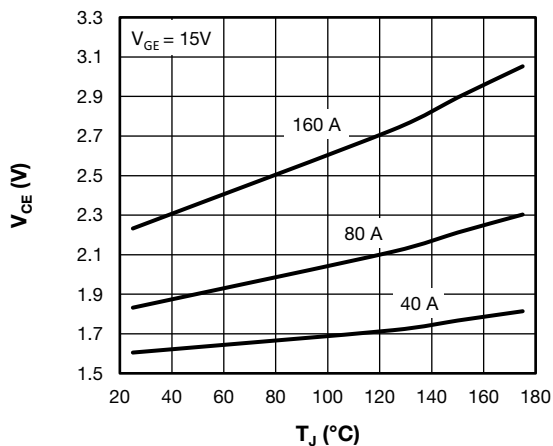
Fig. 2 - Typical IGBT Output Characteristics, $T_J = 125\text{ °C}$ 

Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

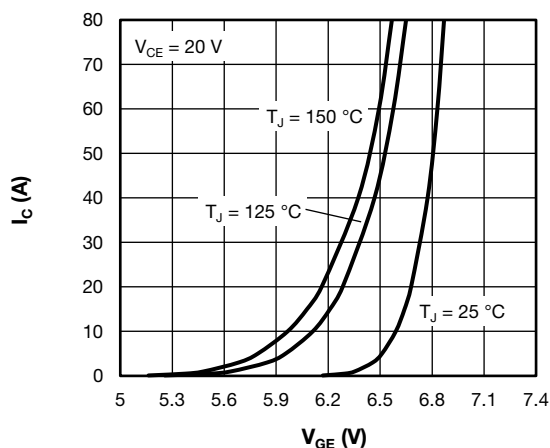


Fig. 5 - Typical IGBT Transfer Characteristics

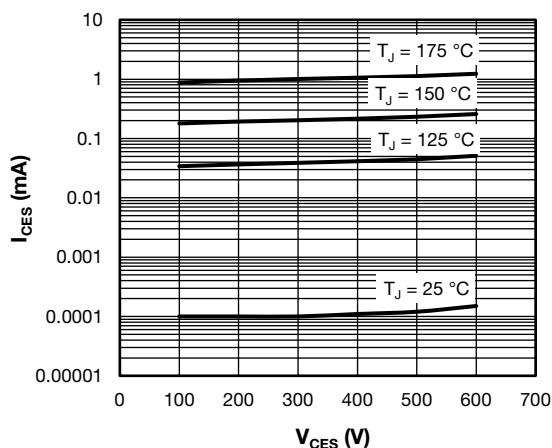


Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current

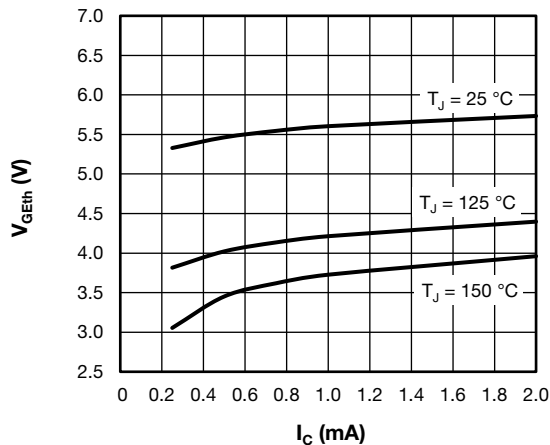


Fig. 6 - Typical IGBT Gate Threshold Voltage

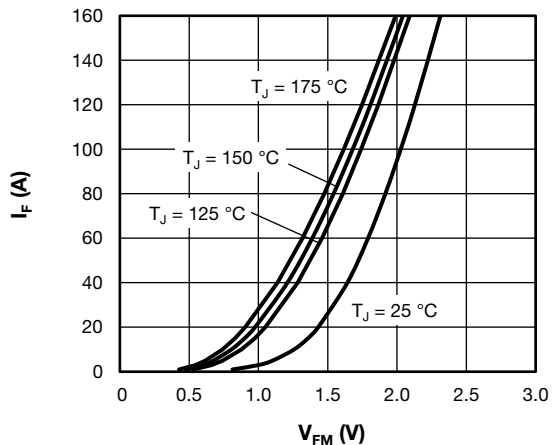


Fig. 9 - Typical Diode Forward Characteristics

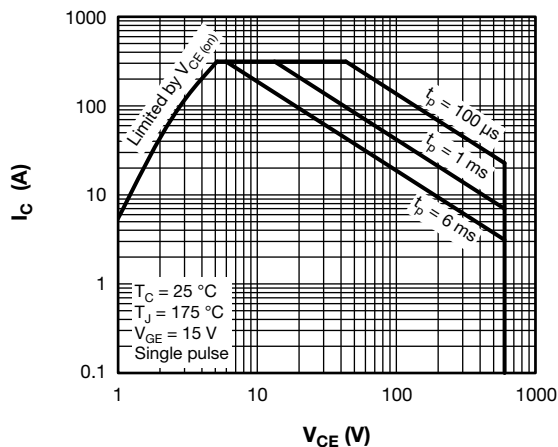


Fig. 7 - IGBT Safe Operating Area

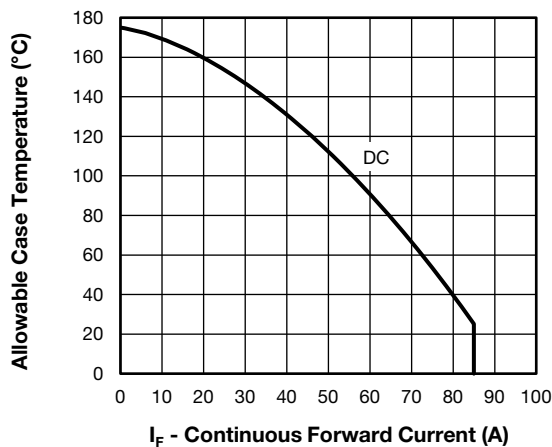


Fig. 10 - Maximum Diode Continuous Forward Current vs. Case Temperature

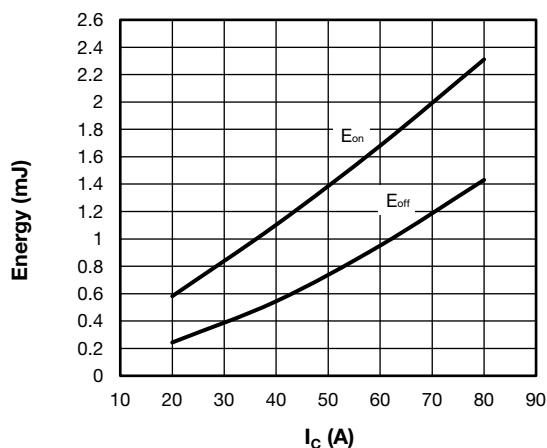


Fig. 11 - Typical IGBT Energy Loss vs. I_C
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 27\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

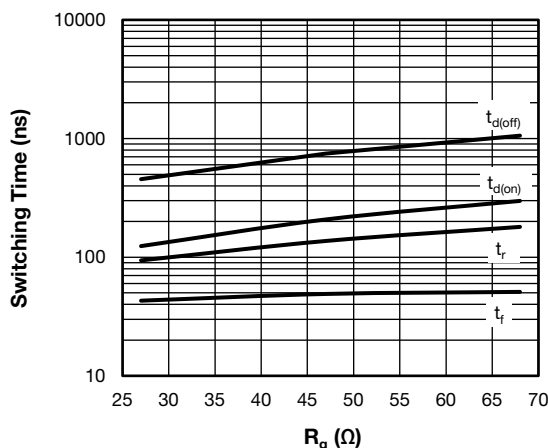


Fig. 14 - Typical IGBT Switching Time vs. R_g
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 80\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

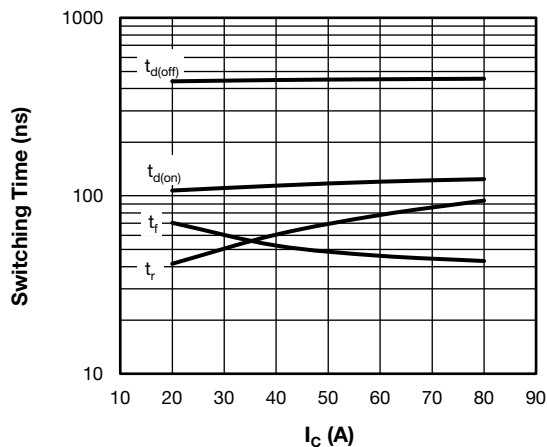


Fig. 12 - Typical IGBT Switching Time vs. I_C
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 27\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

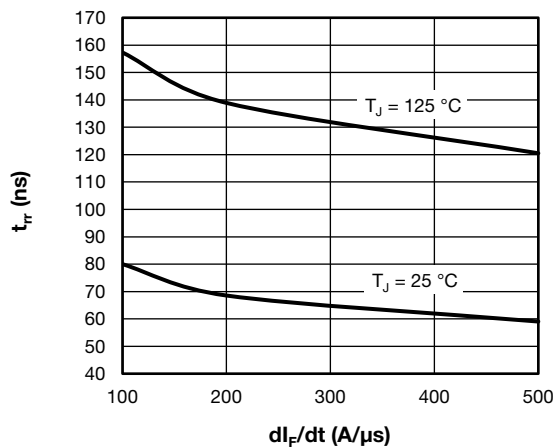


Fig. 15 - Typical t_{rr} Diode vs. dI_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

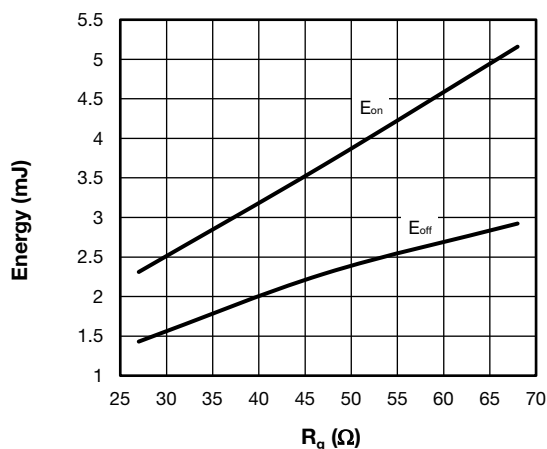


Fig. 13 - Typical IGBT Energy Loss vs. R_g
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 80\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

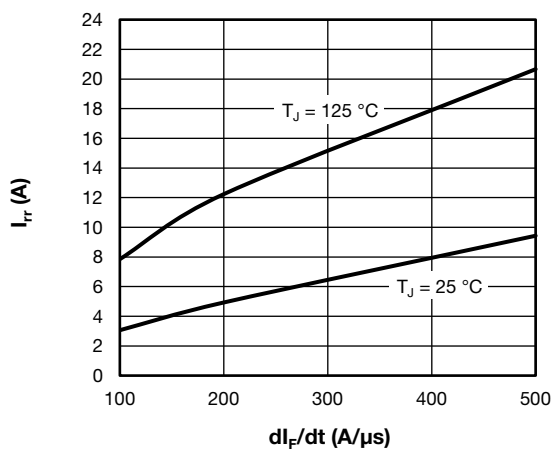


Fig. 16 - Typical I_{rr} Diode vs. dI_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

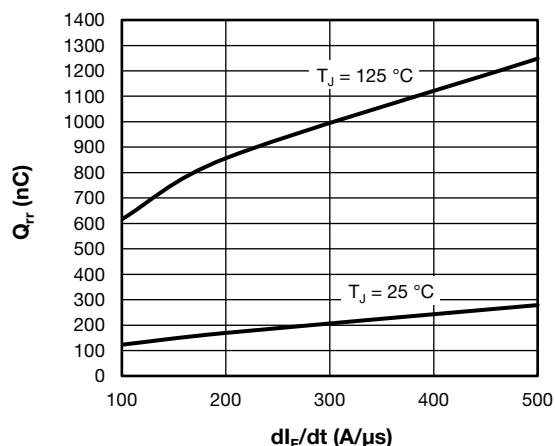


Fig. 17 - Typical Diode Reverse Recovery Charge vs. dI_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

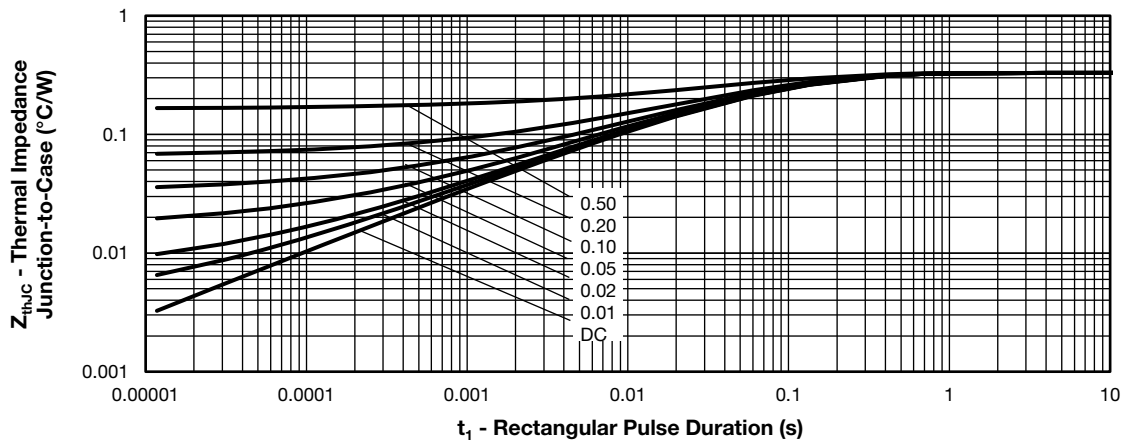


Fig. 18 - Maximum Thermal Impedance Z_{thJC} Characteristics, IGBT

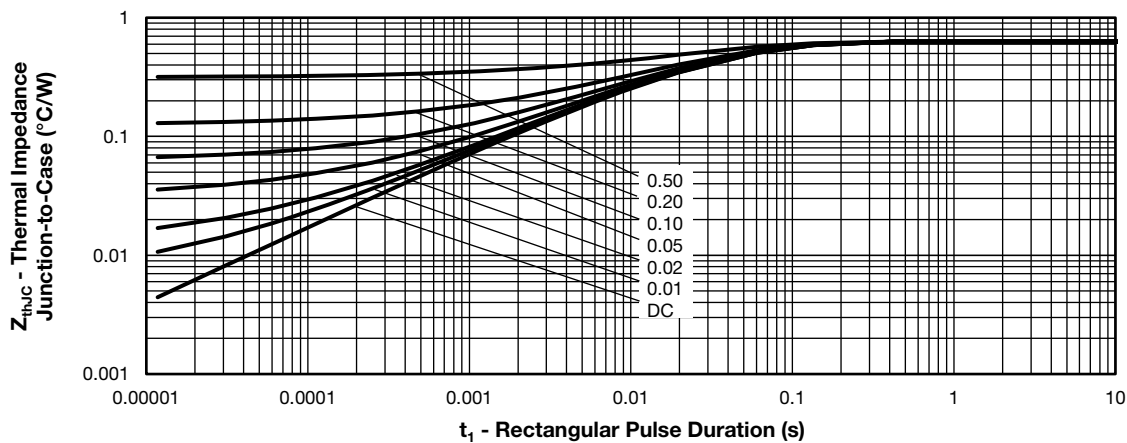


Fig. 19 - Maximum Thermal Impedance Z_{thJC} Characteristics, Diode

ORDERING INFORMATION TABLE

Device code	VS-	G	T	80	D	A	60	U
	1	2	3	4	5	6	7	8

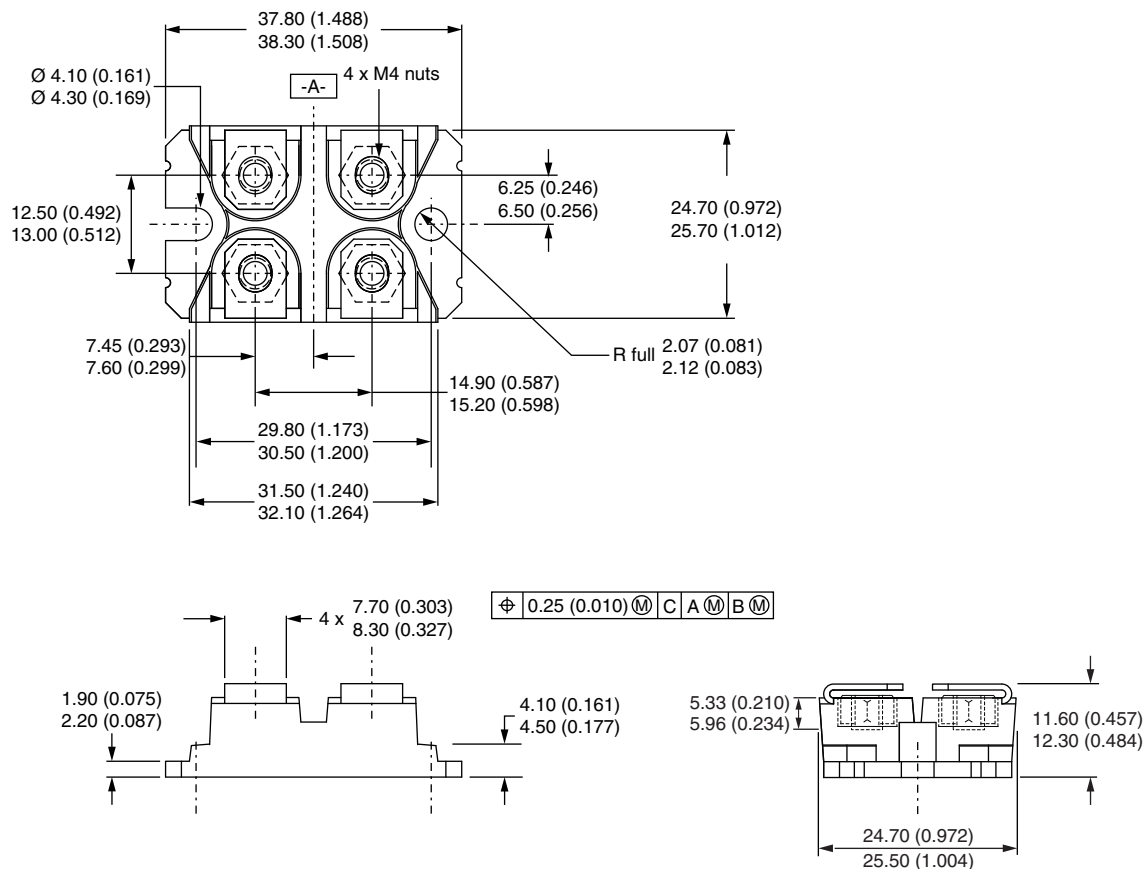
- 1 - Vishay Semiconductors product
- 2 - Insulated gate bipolar transistor (IGBT)
- 3 - T = trench IGBT
- 4 - Current rating (80 = 80 A)
- 5 - Circuit configuration (D = single switch with antiparallel diode)
- 6 - Package indicator (A = SOT-227)
- 7 - Voltage rating (60 = 600 V)
- 8 - Speed / type (U = ultrafast IGBT)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch with AP diode	D	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425

SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter



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